P90FG5R5SL

Power MOSFETs 55V, 90A, N-channel

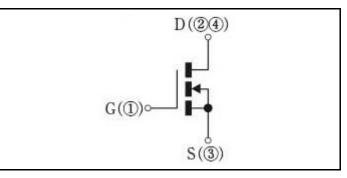
Feature

- N-channel
- SMD
- Low Ron
- 4.5V Gate Drive
- · Low Capacitance
- Pb free terminal
- · RoHS:Yes

OUTLINE



Equivalent circuit



Absolute Maximum Ratings (unless otherwise specified : Tc=25°C)

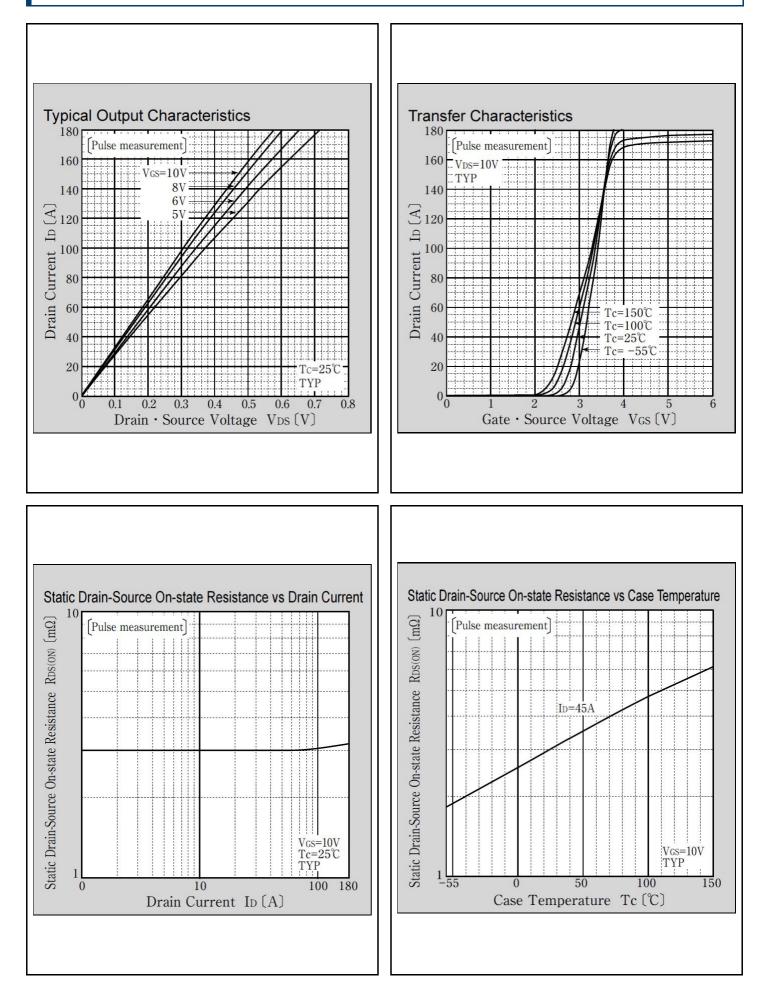
Item	Symbol	Conditions	Ratings	Unit
Storage temperature	Tstg		-55 to 150	°C
Channel tempertature	Tch		150	°C
Drain-source voltage	V _{DSS}		55	V
Gate-source voltage	V _{GSS}		±20	V
Continuous drain current(DC)	I _D		90	А
Continuous drain current(Peak)	I _{DP}	Pulse width 10µs, duty=1/100	360	А
Total power dissipation	P _T		128	W
Single avalanche current	I _{AS}	Starting Tch=25°C Tch≦150°C	52	A
Single avalanche energy	E _{AS}	Starting Tch=25°C Tch≦150°C	272	mJ

* : See the original Specifications

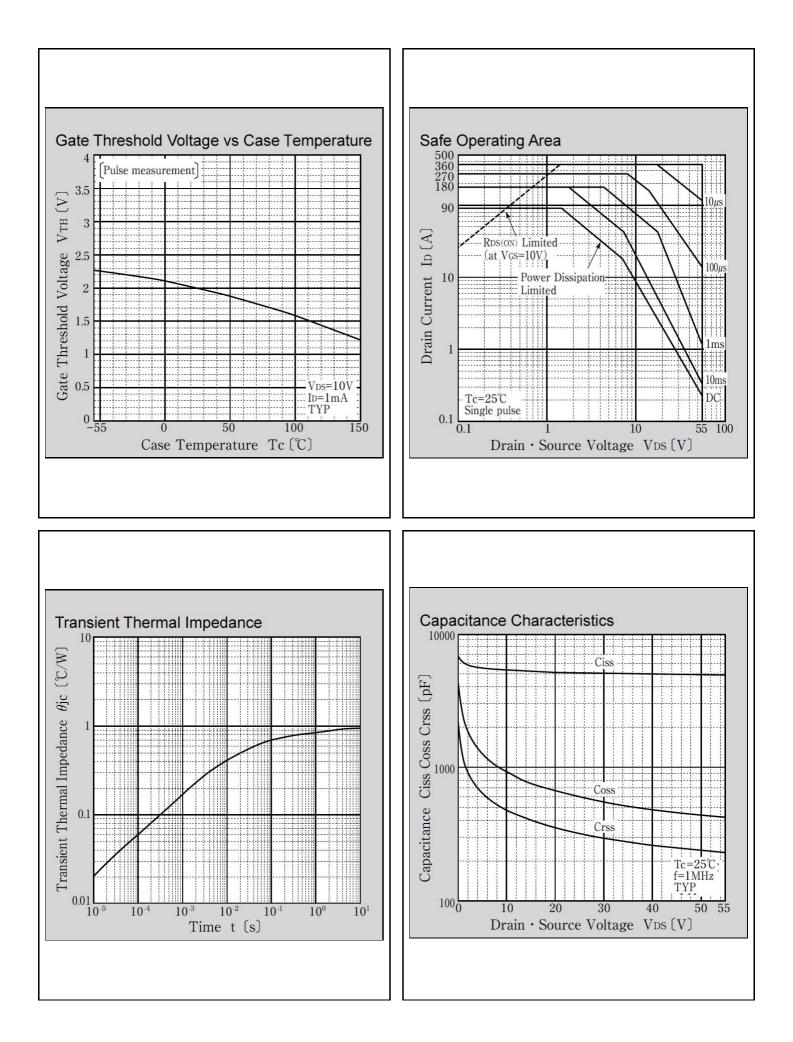
Item	Symbol	Conditions		Ratings		
			MIN	ТҮР	MAX	Unit
Drain-Source breakdown voltage	V _{(BR)DSS}	ID=1mA, VGS=0V	55			V
Zero gate voltage drain current	I _{DSS}	VDS=55V, VGS=0V			1	μA
Gate-source leakage current	I _{GSS}	VGS=±20V, VDS=0V			±0.1	μA
Forward transconductance	g _{fs}	ID=45A, VDS=10V	25			S
Static drain-source on-state resistance	R _{DS(ON)}	ID=45A, VGS=10V		0.003	0.0038	Ω
Static drain-source on-state resistance	R _{DS(ON)}	ID=45A, VGS=4.5V		0.004	0.0054	Ω
Gate threshold voltage	Vth	ID=1mA, VDS=10V	1.5	2	2.5	V
Source-drain diode forward voltage	V _{SD}	IS=90A, VGS=0V			1.5	V
Thermal resistance	Rth(j-c)	Junction to case			0.97	°C/W
Total gate charge	Qg	VDD=44V, VGS=10V, ID=90A		106		nC
Gate to source charge	Qgs	VDD=44V, VGS=10V, ID=90A		19		nC
Gate to drain charge	Qgd	VDD=44V, VGS=10V, ID=90A		34		nC
Input capacitance	Ciss	VDS=25V, VGS=0V, f=1MHz		5130		pF
Reverce transfer capacitnce	Crss	VDS=25V, VGS=0V, f=1MHz		320		pF
Output capacitance	Coss	VDS=25V, VGS=0V, f=1MHz		600		pF
Turn-on delay time	td(on)	ID=45A, RL=0.61Ω, VDD=27.5V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		8		ns
Rise time	tr	ID=45A, RL=0.61Ω, VDD=27.5V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		40		ns
Turn-off delay time	td(off)	ID=45A, RL=0.61Ω, VDD=27.5V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		103		ns
Fall time	tf	ID=45A, RL=0.61Ω, VDD=27.5V, Rg=0Ω, VGS(+)=10V, VGS(-)=0V		67		ns
Diode reverse recovery time	trr	IF=90A, VGS=0V, di/dt=100A/µs		47		ns
Diode reverse recovery charge	Qrr	IF=90A, VGS=0V, di/dt=100A/µs		70		nC

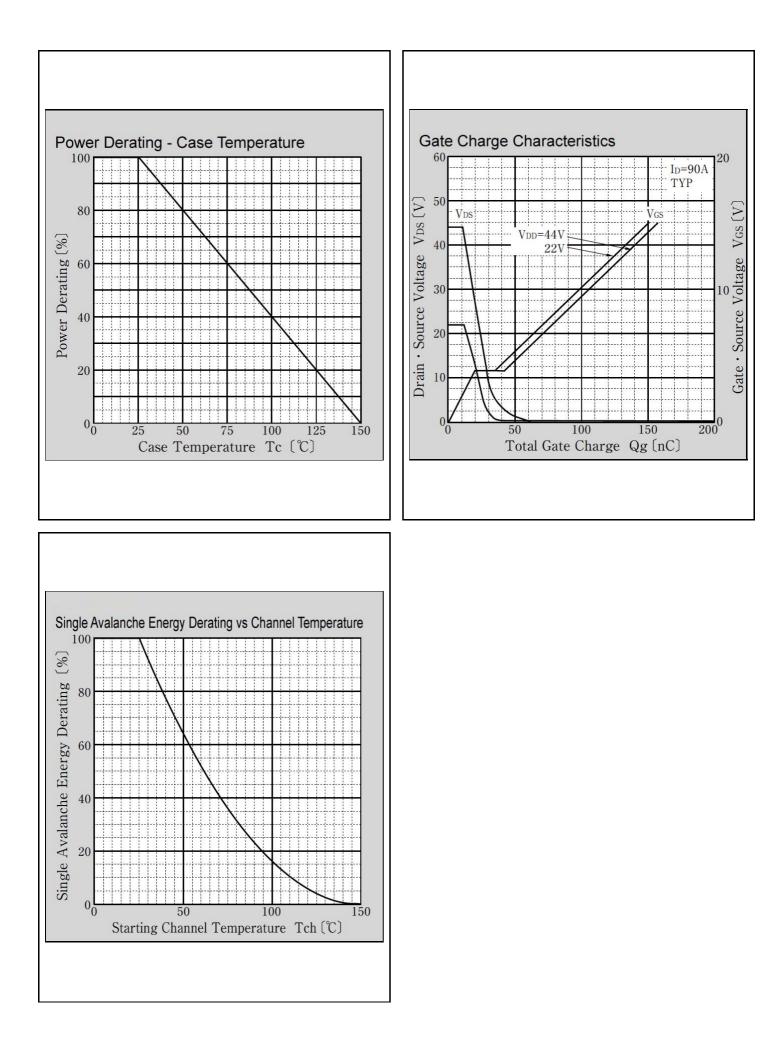
* : See the original Specifications

CHARACTERISTIC DIAGRAMS



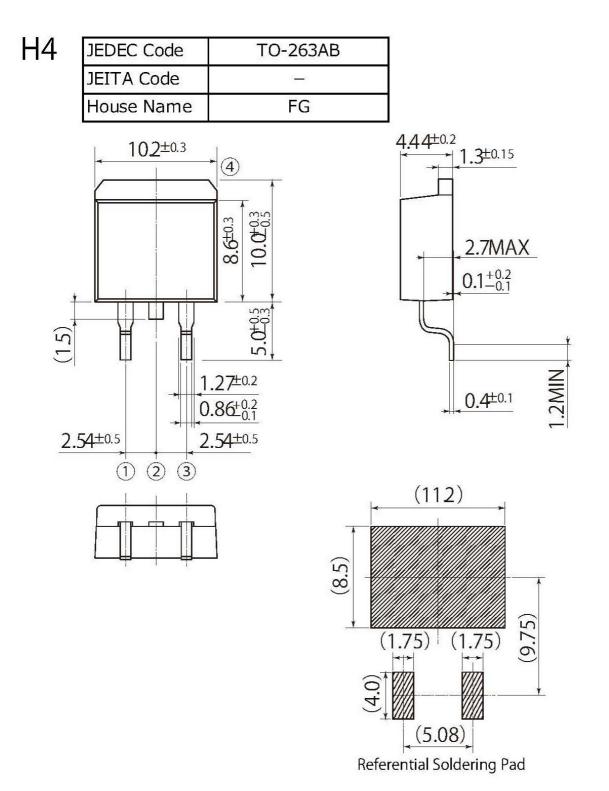
3/7





unit:mm

scale: 3/1



Optimize soldering pad to the board design and soldering condition.

Notes

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